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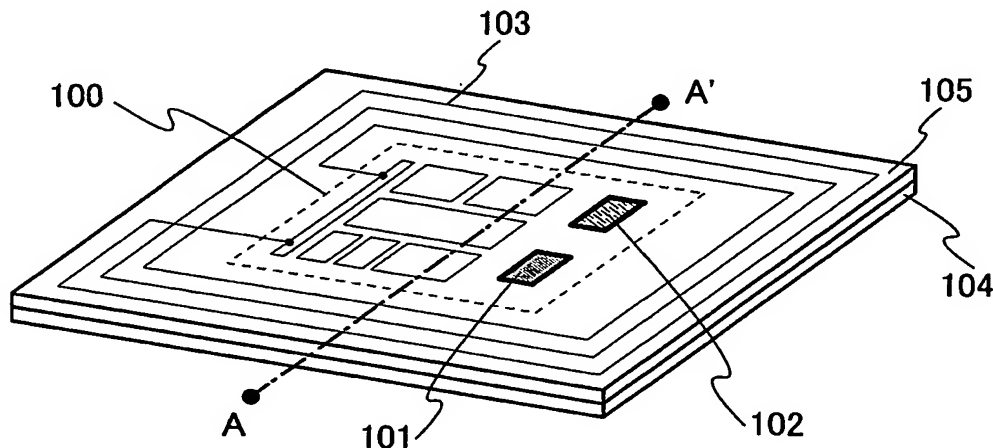
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ning of each regular issue of the PCT Gazette.

(54) Title: ID CHIP AND IC CARD



(57) Abstract: The present invention provides an ID chip or an IC card in which the mechanical strength of an integrated circuit can be enhanced without suppressing a circuit scale. An ID chip or an IC card of the present invention has an integrated circuit in which a TFT (a thin film transistor) is formed from an insulated thin semiconductor film. Further, an ID chip or an IC card of the present invention has a light-emitting element and a light-receiving element each using a non-single-crystal thin film for a layer conducting photoelectric conversion. Such a light-emitting element or a light-receiving element may be formed consecutively to (integrally with) an integrated circuit or may be formed separately and attached to an integrated circuit.